

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	821376	(el or electroluminescent)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:21
L4	36633	(el or electroluminescent) near3 display	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:22
L5	336811	temperature near (chang\$4 or variat\$4 or varies or vary)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:23
L6	216762	(tft or thin adj film or transistor\$1) with saturation sam (constant adj current)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:24
L7	1499	(tft or thin adj film or transistor\$1) with saturation same (constant adj current)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:24
L8	1063	4 and 5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:24
L9	13	7 and 8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:24

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L2	0	((driving adj display adj device) with (pixel\$1) with (EL adj element) with (tft or thin adj film adj transistor\$1) and (driv\$3 adj one adj frame adj period) with (plural adj sub-frame\$1 adj period\$1) and (apply\$3 adj one adj first adj gate adj voltage) and (second adj gate adj voltage) with (gate adj electrode\$1) with (tft or thin adj film adj transistor\$1) with (during adj each adj plural adj sub-frame\$1 adj period\$1) and (drain adj current) with (tft or thin adj film adj transistor\$1) with flow\$1 adj between with (electrode\$1) with (EL adj element\$1) and (EL adj element\$1) with (emitting adj state) same (first adj gate adj voltage) with applied with (gate adj electrode\$1) with (tft or thin adj film adj transistor\$1) and (tft or thin adj film adj transistor\$1) with (non-conductive adj state) and (EL adj element\$1) with (non-emitting adj state) with (second adj gate adj voltage) same applied same (gate adj electrode\$1) with (tft or thin adj film adj transistor\$1) and (tft or thin adj film adj transistor\$1) with operat\$3 with saturat\$3 with region same (drain adj current) adj constant with (temperature adj variations)).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 21:21